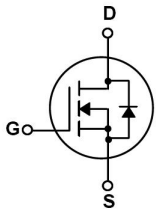
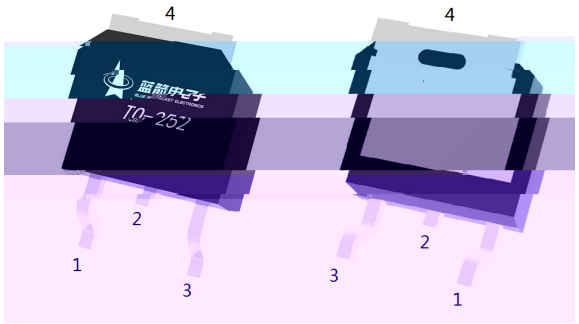
TO-252 .> / / x 4 ?ú 3 MOS « | • ’ož
N-CHANNEL MOSFET in a TO-252 Plastic Package.

V_{DS} (V) = 150V
I_D =25A (V_{GS} = f 20V)
$R_{DS(ON)}$@10V 0 40mR
—)í D } Ä . , 6 X U J [I Z

*) *) y ') *) ô E ˜ c 5 … v k ’ y W œ Y *) *) ô E ˜ož
Synchronus Rectification in DC/DC and AC/DC Converters,Isolated DC/DC Converters in Telecom and Industrial.





PIN1 y G PIN 2 y D PIN 3 y S PIN 4 y D

, M V / Marking

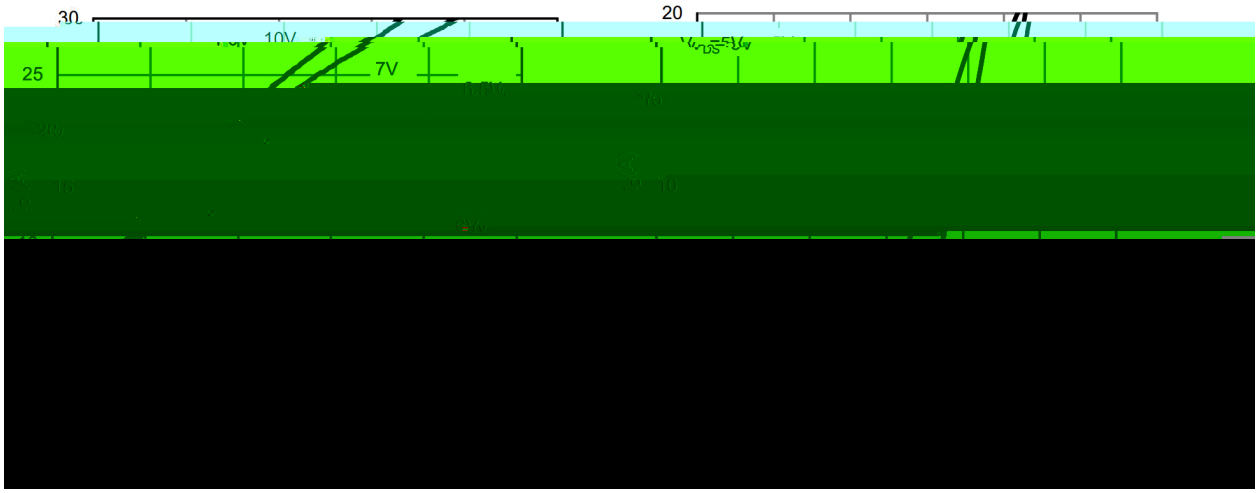
• - ~ ª ¢ož

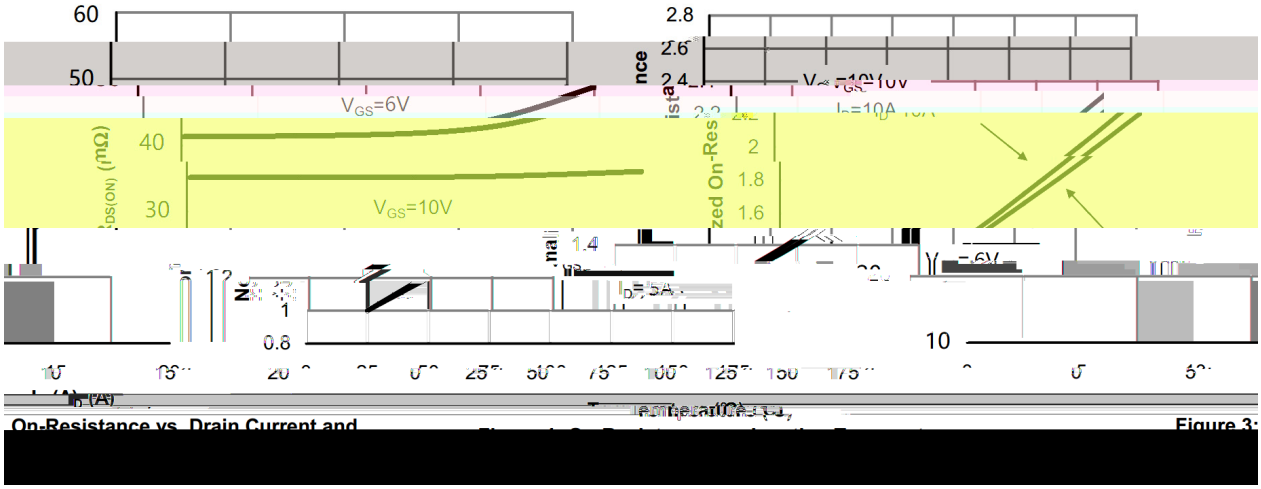
@ ƒ Parameter		… Z Symbol	ƒ › Rating	% y Unit
Drain-Source Voltage		V_{DSS}	150	V
Drain Current		I_D(Tc=25)	25	A
Drain Current - Pulsed		I_{DM}	49	A
Gate-Source Voltage		V_{GS}	±20	V
Single Pulsed Avalanche Energy		E_{AS}	18.4	mJ
Avalanche Current		I_{AS}	7.0	A
Power Dissipation		P_D(Tc=25)	50	W
Operating and Storage Temperature Range		T_J,T_{stg}	-55 to 150	
Junction-to-Ambient	t 0 10	R JA	25	/W
Junction-to-Ambient	Steady-State		55	
Junction-to-Case	Steady-State	R JC	2.3	

@ ƒ Parameter	… Z Symbol	y ¡ Ú ^ Test Conditions	Â 4 › Min	Á º › Typ	Â Ý › Max	% y Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250 A	150	160		V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=120V V_{GS}=0V			1	A

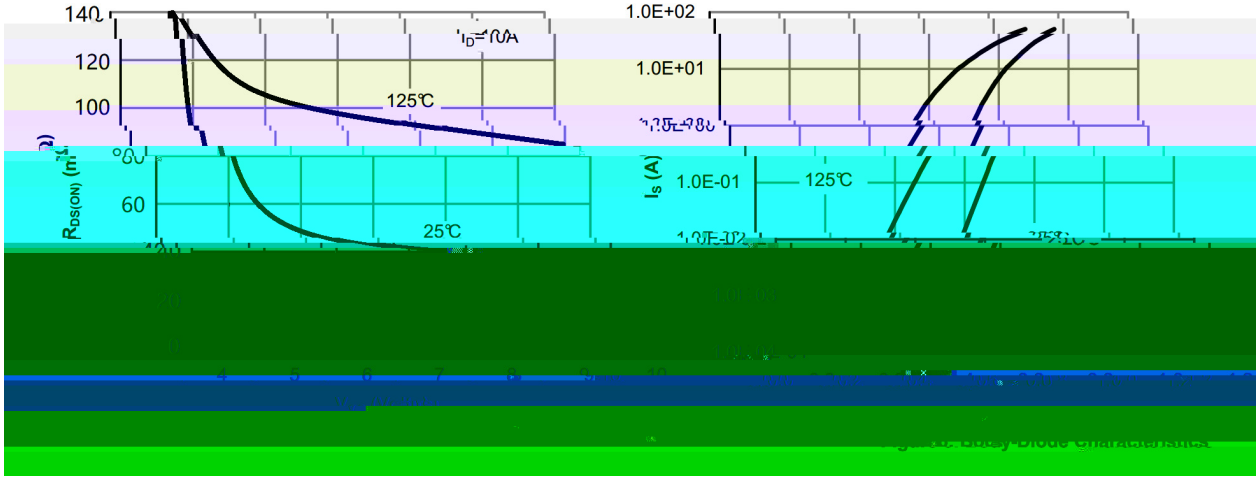
@ ƒ	… Z	y ¡ Ú ^	Â 4 ›	Á º ›
Parameter	Symbol	Test Conditions	Min	Typ

Ô ? d • Ž ¢ / Electrical Characteristic Curve





On-Resistance vs. Drain Current and Figure 3:



Ô ? d • Ž ¢ Electrical Characteristic Curve

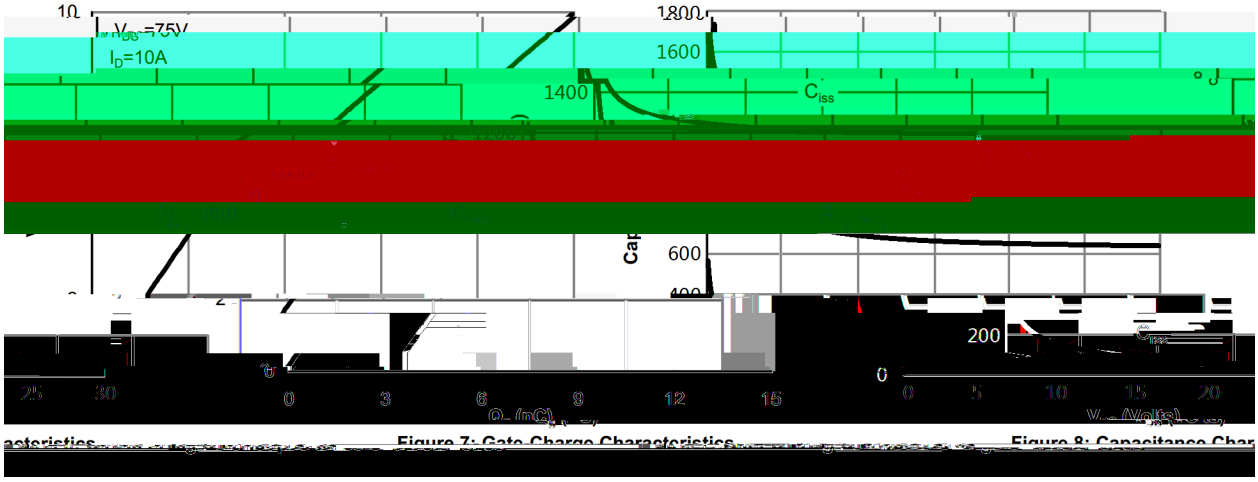
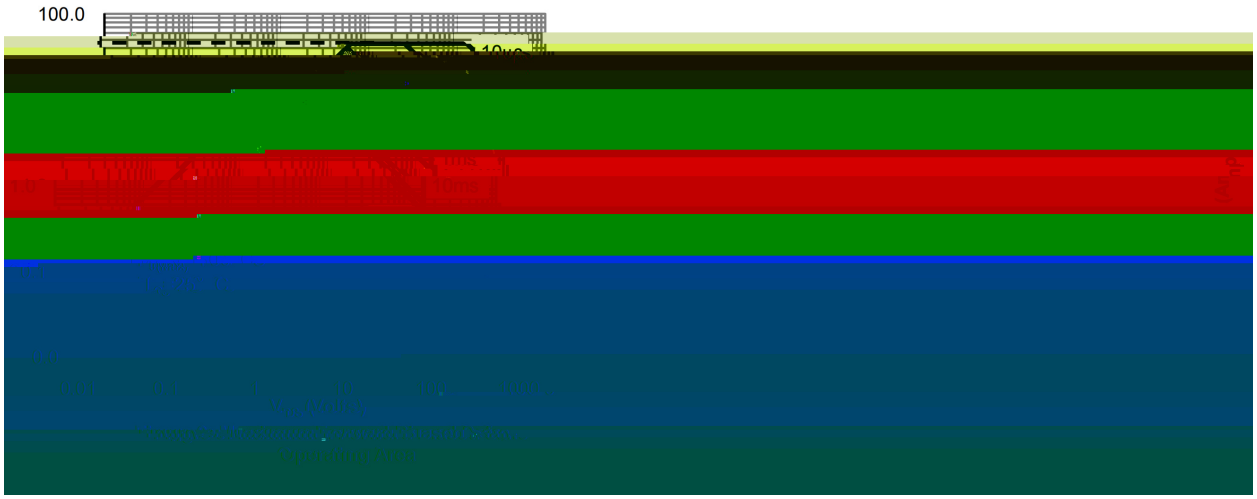


Figure 7: Gate Charge Characteristics Figure 8: Capacitance Char



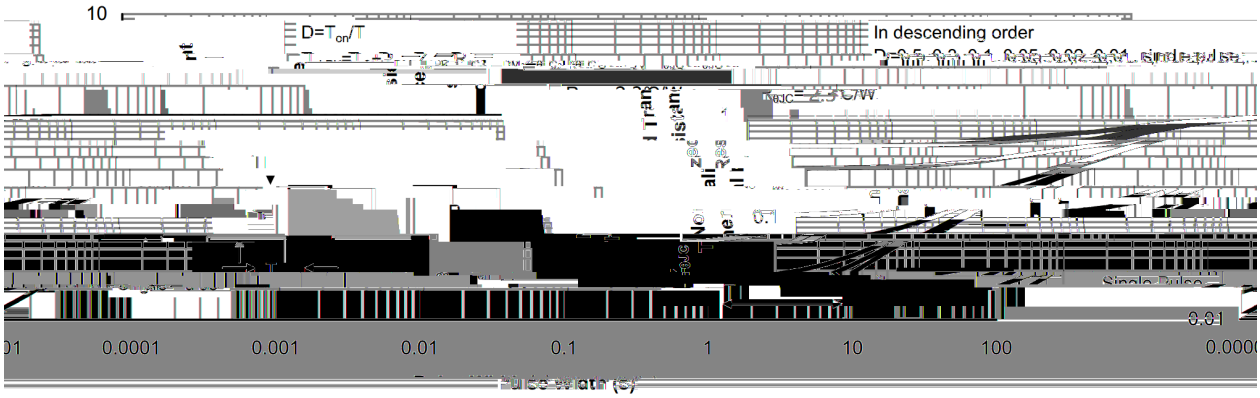
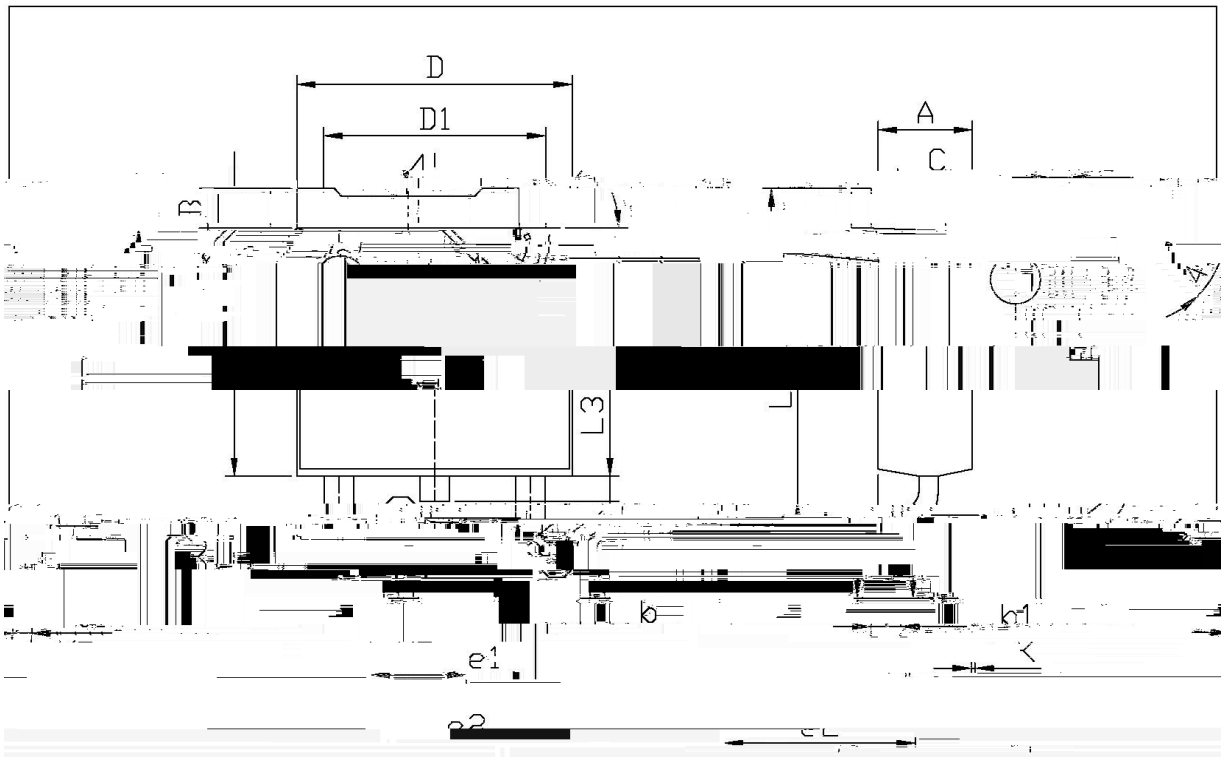


Figure 10: Normalized Maximum Transient Thermal Impedance

Ø ¤ =) ¢ / Package Dimensions

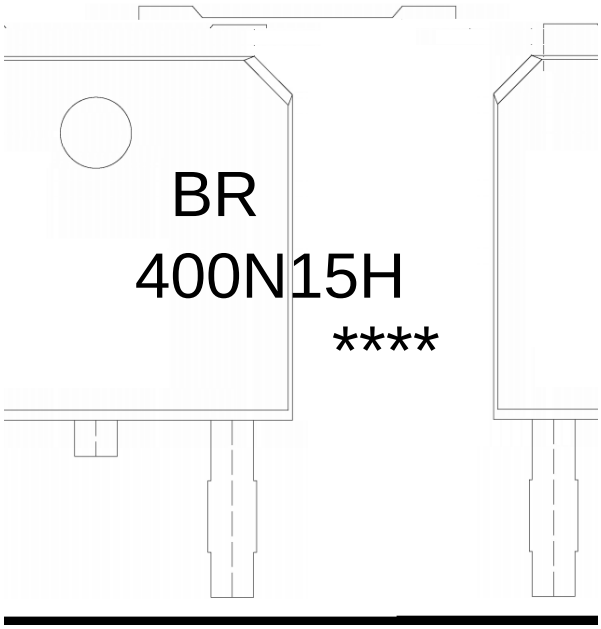


单位：mm

Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
B	0.95	1.25	e1	2.24	2.34
h	0.70	0.90	k	4.78	4.98
b	0.45	0.55	k1	0.85	1.35
c	0.46	0.61	L	1.40	1.78
D	6.45	6.75	L3	0.60	0.90
D1	5.10	5.50	K	0.00	0.10

TO-252

, M y ƒ / Marking Instructions



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Note:

BR:	Company Code
400N15H:	Product Type
****:	Lot No. Code, code change with Lot No